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(54) **Title:** HEATING DEVICE AND SEMICONDUCTOR PROCESSING APPARATUS

(54) 发明名称: 一种加热装置及半导体处理设备

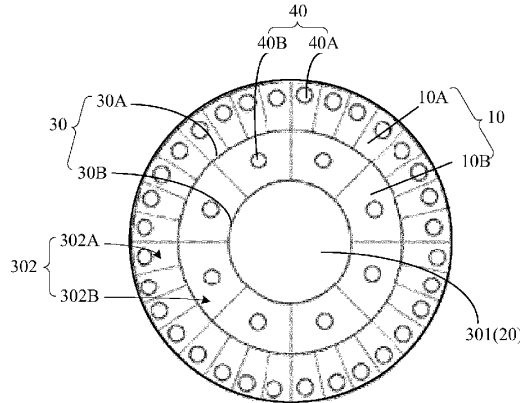


图 3

(57) **Abstract:** Disclosed in the present application are a heating device and a semiconductor processing apparatus. The heating device is located on one side of a base in a height direction, and has a central region and a plurality of annular regions; and the heating device comprises, in each annular region, a plurality of heating lamps, which are evenly arranged in the circumferential direction of the annular region, and an annular reflecting plate, which is located on the sides of the plurality of heating lamps away from the base, and the heating device comprises reflecting assemblies, which are respectively located on the sides of the annular regions close to the central region, wherein each reflecting assembly comprises a plurality of reflecting plates, which correspond on a one-to-one basis to the plurality of heating lamps in the corresponding annular region; the reflecting plates extend in a direction from the annular reflecting plates to the base, so as to limit light from the corresponding heating lamps to be irradiated on preset regions of the base; and the reflecting assemblies are configured to make the preset regions corresponding to the plurality of heating lamps be located in different radial ranges of the

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PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW。

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base. In the present application, light can be prevented from being concentratedly irradiated on the same region and causing a cliff-like distribution of the illumination in a radius direction, thereby realizing a gradual change in light intensity, such that the uniformity of heating can be improved.

(57) 摘要: 本申请公开了一种加热装置及半导体处理设备，加热装置位于基座在高度方向上的一侧，具有中心区域和多个环形区域；加热装置包括在每一环形区域，沿环形区域周向均匀设置的多个加热灯和位于多个加热灯远离基座一侧的环形反射板；以及，位于每一环形区域的靠近中心区域一侧的反射组件；反射组件包括与对应的环形区域内的多个加热灯一一对应的多个反射板；反射板由环形反射板向基座的方向延伸，以限定对应的加热灯的光照射在基座的预设区域内；反射组件用于使多个加热灯对应的预设区域位于基座的不同径向范围内。本申请可以避免光线集中照射在同一区域而使光照沿半径方向呈断崖式分布，从而实现光照强度的渐变，可以提高加热的均匀性。